

## SWITCHING REGULATOR APPLICATIONS

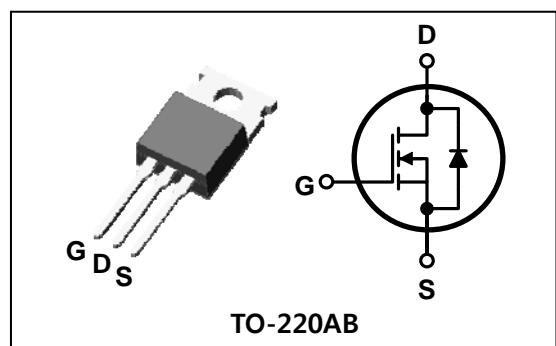
### Features

- High Voltage :  $BV_{DSS}=400V$ (Min.)
- Low  $C_{rss}$  :  $C_{rss}=14pF$ (Typ.)
- Low gate charge :  $Q_g=16nC$ (Typ.)
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=1.0\Omega$ (Max.)

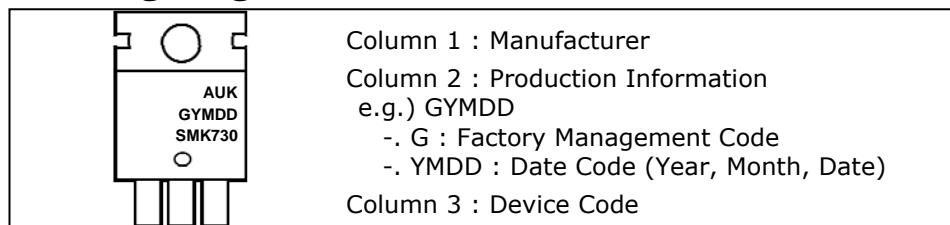
### Ordering Information

Type No.	Marking	Package Code
SMK730P	SMK730	TO-220AB

### PIN Connection



### Marking Diagram



### Absolute maximum ratings ( $T_c=25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	400	V
Gate-source voltage	$V_{GSS}$	$\pm 30$	V
Drain current (DC) *	$I_D$	$T_c=25^\circ C$	A
		$T_c=100^\circ C$	A
Drain current (Pulsed) *	$I_{DM}$	22	A
Power dissipation	$P_D$	70	W
Avalanche current (Single) ②	$I_{AS}$	5.5	A
Single pulsed avalanche energy ②	$E_{AS}$	449	mJ
Avalanche current (Repetitive) ①	$I_{AR}$	5.5	A
Repetitive avalanche energy ①	$E_{AR}$	8.5	mJ
Junction temperature	$T_J$	150	$^\circ C$
Storage temperature range	$T_{stg}$	-55~150	

\* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max.	Unit
Thermal resistance	$R_{th(J-C)}$	-	1.78	$^\circ C/W$
	$R_{th(J-A)}$	-	62.5	

**Electrical Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

<b>Characteristic</b>	<b>Symbol</b>	<b>Test Condition</b>	<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>	<b>Unit</b>
Drain-source breakdown voltage	$\text{BV}_{\text{DSS}}$	$I_D=250\mu\text{A}, V_{GS}=0$	400	-	-	V
Gate threshold voltage	$V_{GS(\text{th})}$	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$	2.0	-	4.0	V
Drain-source cut-off current	$I_{\text{DSS}}$	$V_{DS}=400\text{V}, V_{GS}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate leakage current	$I_{\text{GSS}}$	$V_{DS}=0\text{V}, V_{GS}=\pm 30\text{V}$	-	-	$\pm 100$	nA
Drain-source on-resistance <sup>(4)</sup>	$R_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=2.75\text{A}$	-	0.8	1.0	$\Omega$
Forward transfer conductance <sup>(4)</sup>	$g_{fs}$	$V_{DS}=10\text{V}, I_D=2.75\text{A}$	-	3.8	-	S
Input capacitance	$C_{iss}$	$V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1\text{MHz}$	-	732	915	pF
Output capacitance	$C_{oss}$		-	91	114	
Reverse transfer capacitance	$C_{rss}$		-	14.0	17.5	
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD}=250\text{V}, I_D=5.5\text{A}$ $R_G=25\Omega$	-	12	-	ns
Rise time	$t_r$		-	46	-	
Turn-off delay time	$t_{d(\text{off})}$		-	50	-	
Fall time	$t_f$		-	48	-	
Total gate charge	$Q_g$	$V_{DS}=320\text{V}, V_{GS}=10\text{V}$ $I_D=5.5\text{A}$	-	16	20	nC
Gate-source charge	$Q_{gs}$		-	5.1	-	
Gate-drain charge	$Q_{gd}$		-	3.7	-	

**Source-Drain Diode Ratings and Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

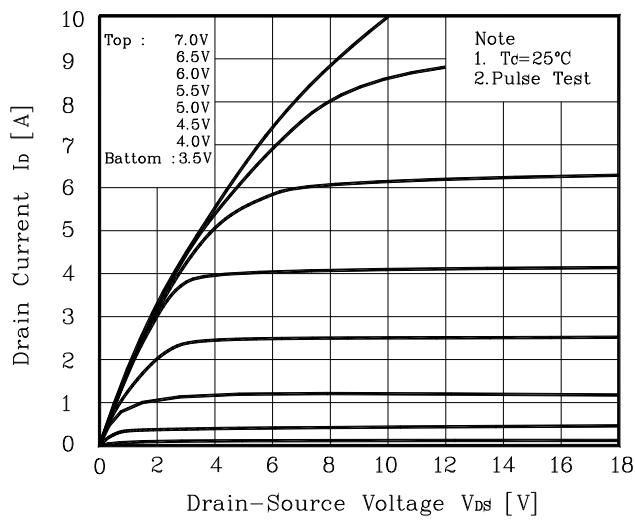
<b>Characteristic</b>	<b>Symbol</b>	<b>Test Condition</b>	<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>	<b>Unit</b>
Source current (DC)	$I_S$	Integral reverse diode in the MOSFET	-	-	5.5	A
Source current (Pulsed) <sup>(1)</sup>	$I_{SM}$		-	-	22	
Forward voltage <sup>(4)</sup>	$V_{SD}$	$V_{GS}=0\text{V}, I_S=5.5\text{A}$	-	-	1.4	V
Reverse recovery time	$t_{rr}$	$I_S=5.5\text{A}, V_{GS}=0\text{V}$ $dI_F/dt=100\text{A}/\mu\text{s}$	-	270	-	ns
Reverse recovery charge	$Q_{rr}$		-	1.9	-	uC

Note :

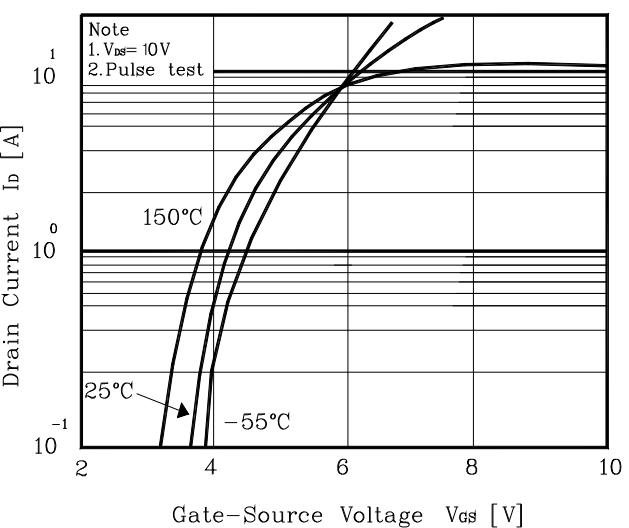
- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ② L=26mH,  $I_{AS}=5.5\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$
- ③ Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$
- ④ Essentially independent of operating temperature

## Electrical Characteristic Curves

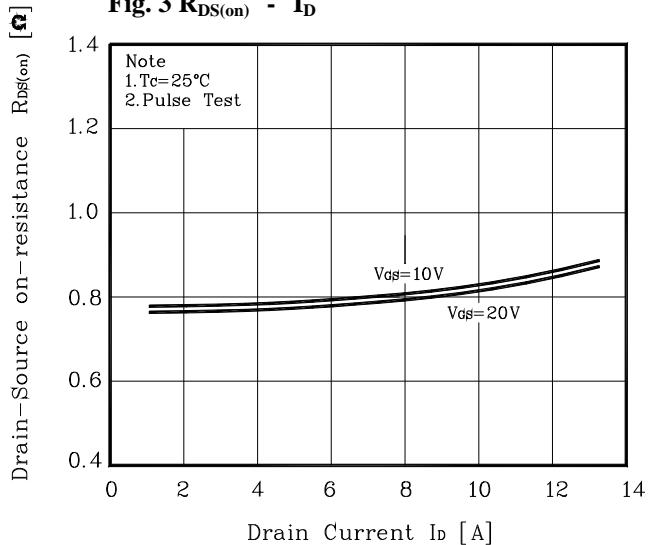
**Fig. 1  $I_D$  -  $V_{DS}$**



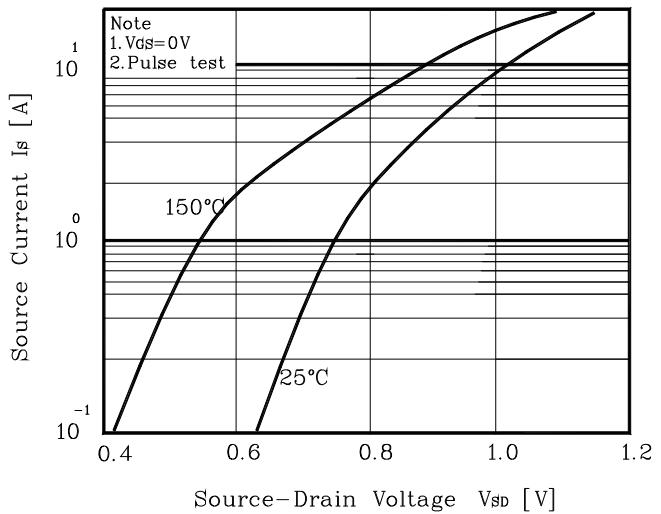
**Fig. 2  $I_D$  -  $V_{GS}$**



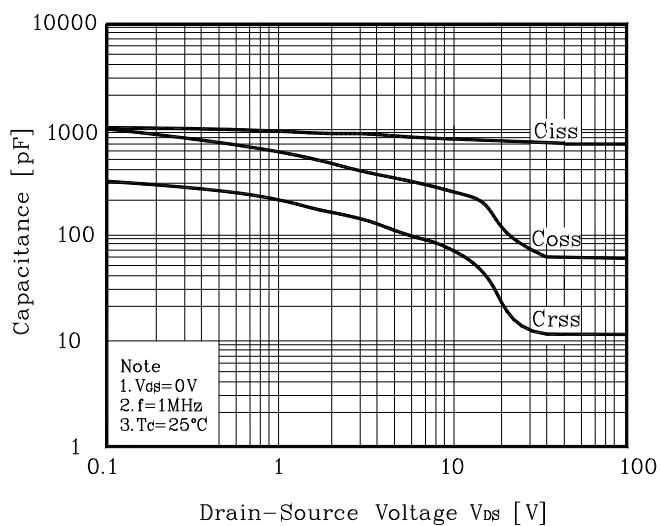
**Fig. 3  $R_{DS(on)}$  -  $I_D$**



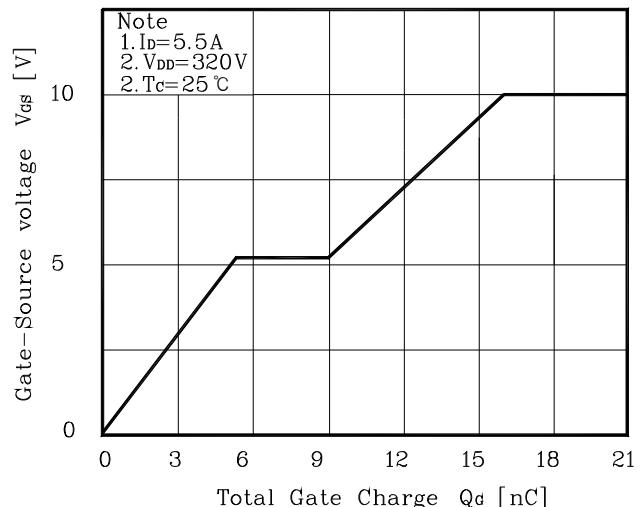
**Fig. 4  $I_S$  -  $V_{SD}$**



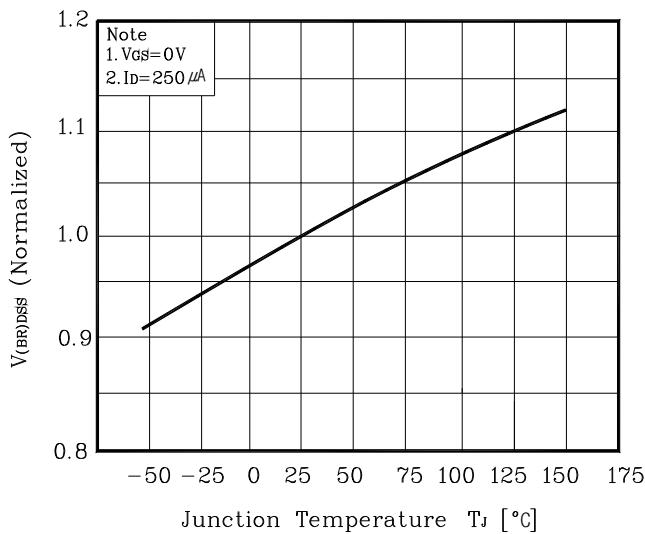
**Fig. 5 Capacitance -  $V_{DS}$**



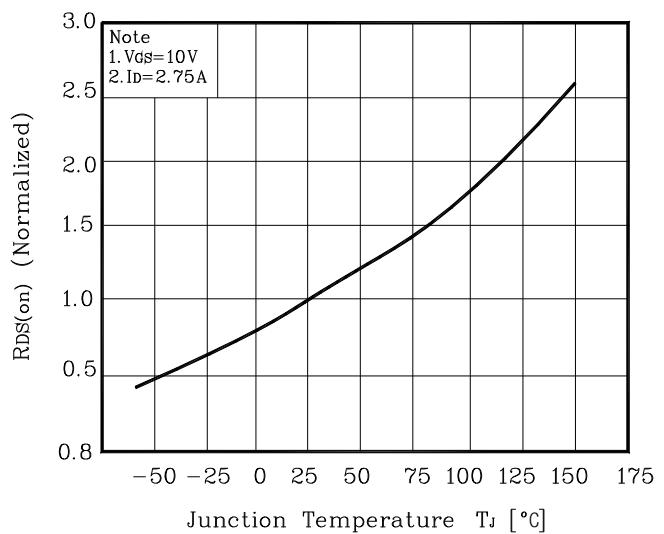
**Fig. 6  $V_{GS}$  -  $Q_G$**



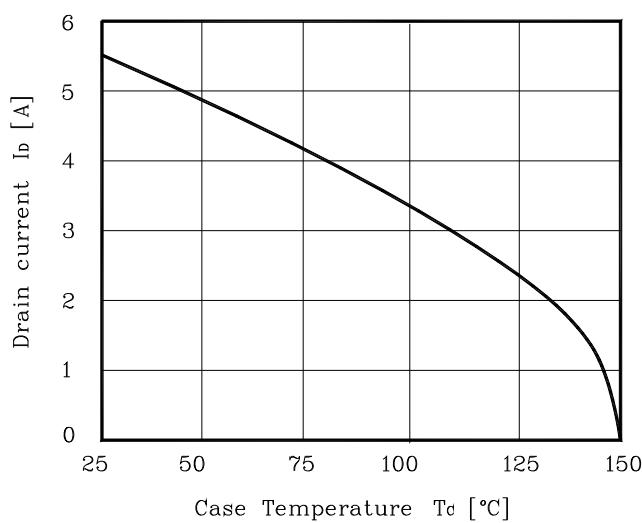
**Fig. 7  $V_{(BR)DSS}$  -  $T_J$**



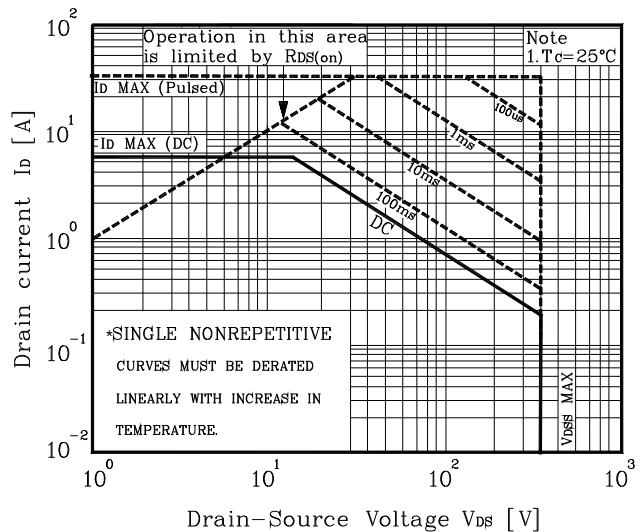
**Fig. 8  $R_{DS(on)}$  -  $T_J$**



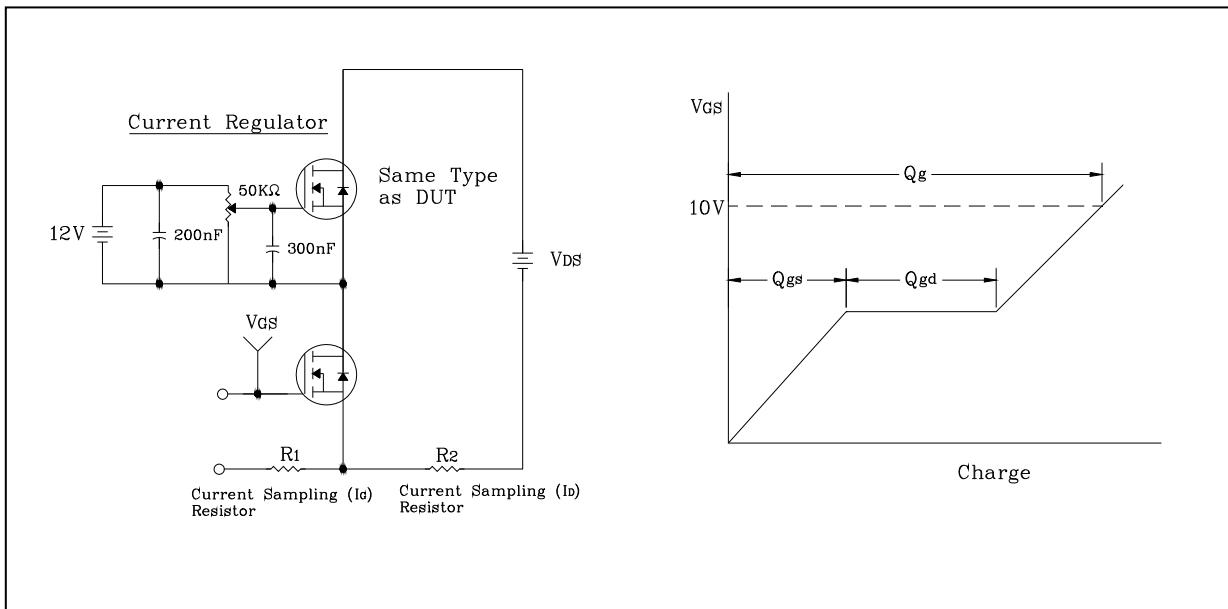
**Fig. 9  $I_D$  -  $T_C$**



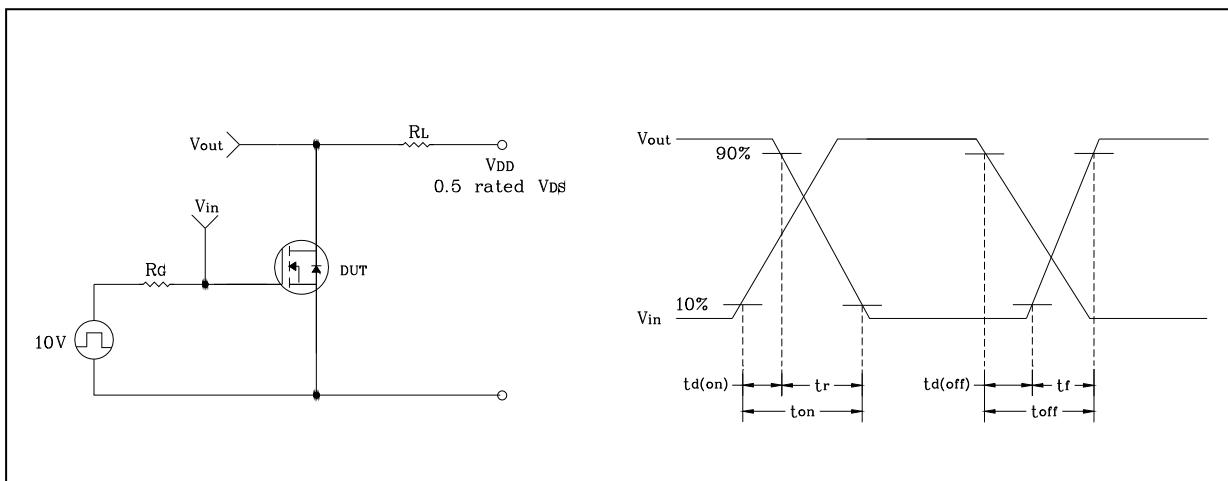
**Fig. 10 Safe Operating Area**



**Fig. 11 Gate Charge Test Circuit & Waveform**



**Fig. 12 Resistive Switching Test Circuit & Waveform**



**Fig. 13 E<sub>AS</sub> Test Circuit & Waveform**

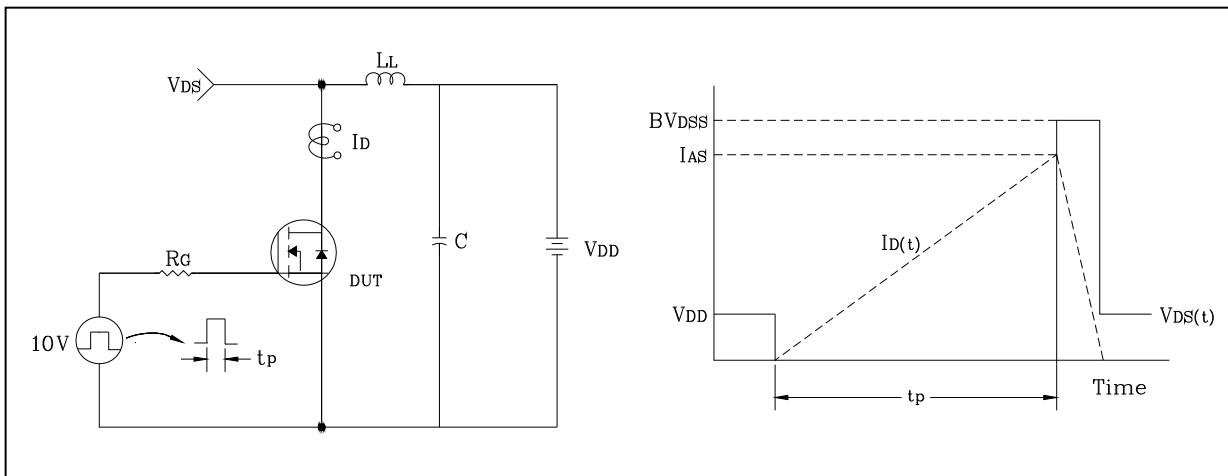
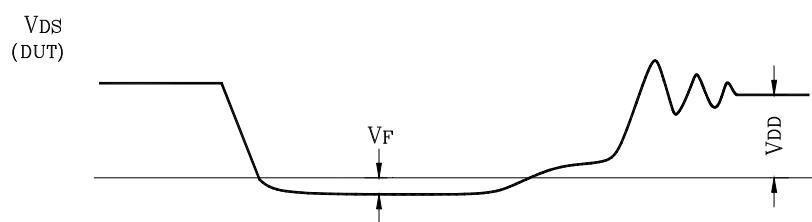
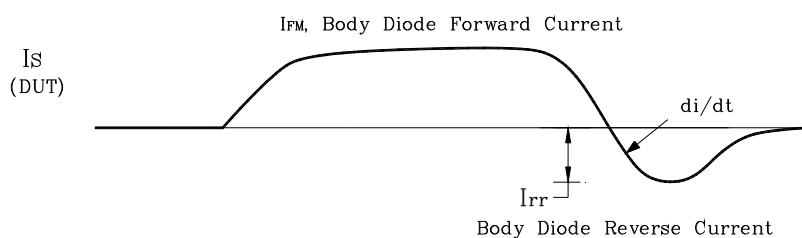
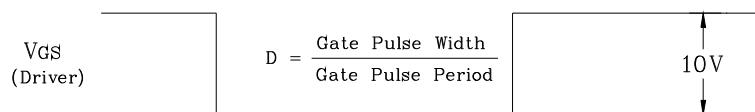
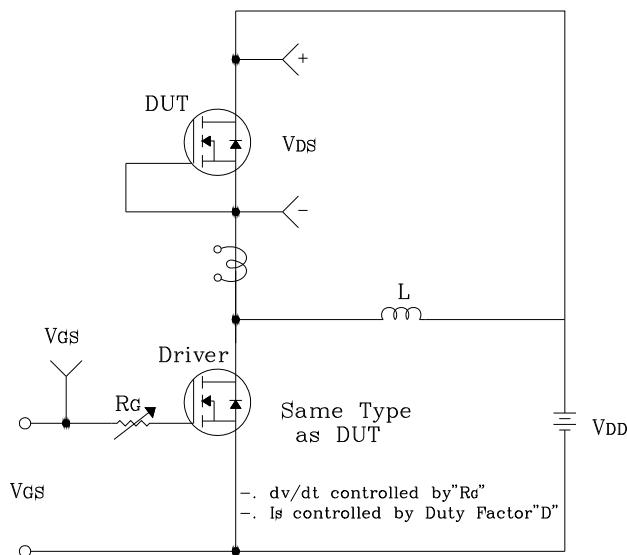
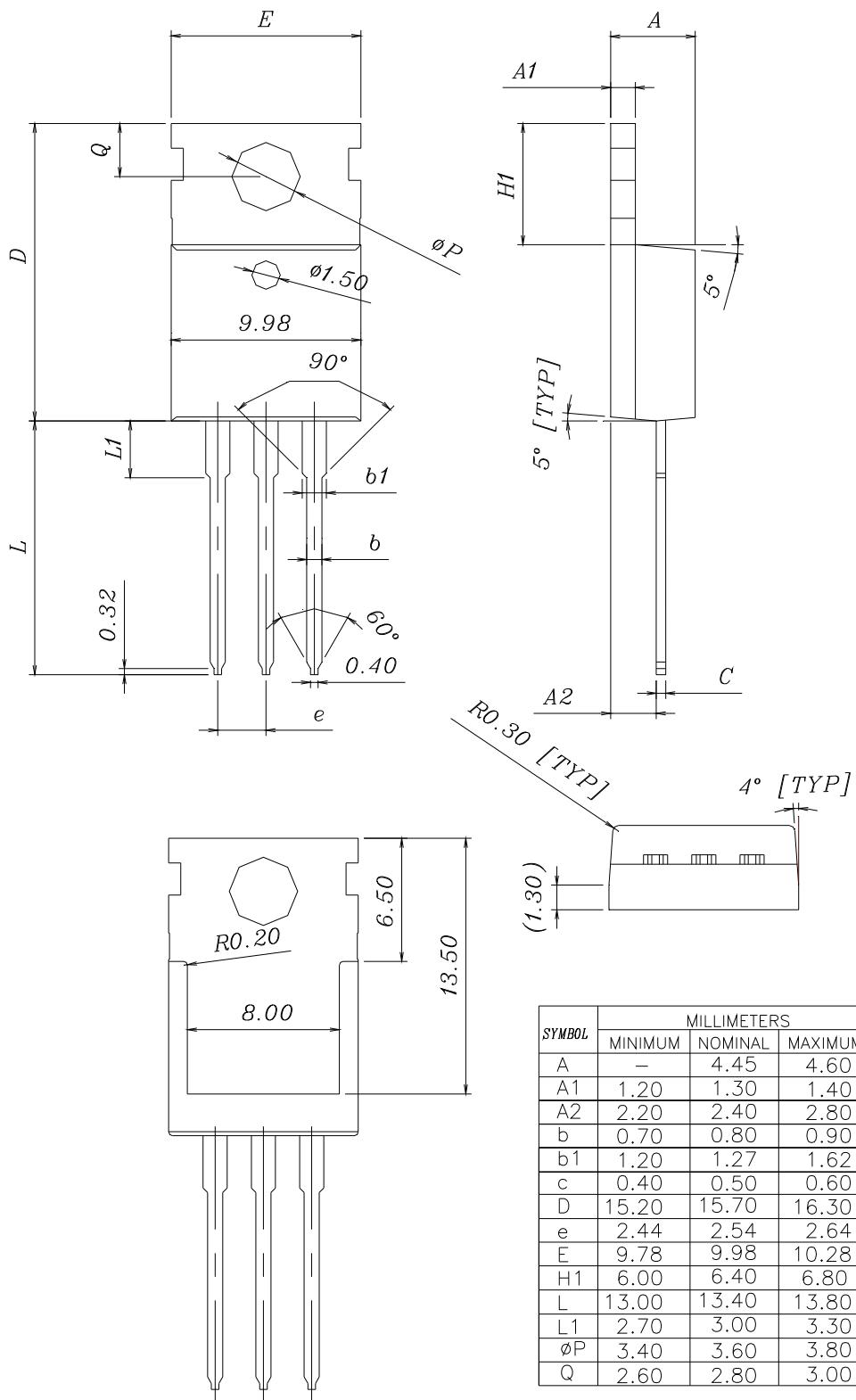


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



## Outline Dimension

unit: mm



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	—	4.45	4.60	
A1	1.20	1.30	1.40	
A2	2.20	2.40	2.80	
b	0.70	0.80	0.90	
b1	1.20	1.27	1.62	
c	0.40	0.50	0.60	
D	15.20	15.70	16.30	
e	2.44	2.54	2.64	
E	9.78	9.98	10.28	
H1	6.00	6.40	6.80	
L	13.00	13.40	13.80	
L1	2.70	3.00	3.30	
$\phi P$	3.40	3.60	3.80	
Q	2.60	2.80	3.00	

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